

L Number	Hits	Search Text	DB	Time stamp
3	1422619	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:17
4	424825	LED\$1 near3 chip) (light\$3 near3 emitt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:27
5	426835	LED\$1 with chip) (light\$3 near3 emitt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:27
6	94753	semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:27
7	16037	(GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:18
8	1843	((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:19
9	503	((((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)) & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:40
10	463	(((((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)) & solder\$3) & substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:40
11	371	(((((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)) & solder\$3) & substrate) & higher	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:29
12	39	(((((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)) & solder\$3) & substrate) & higher) & ((thermal near3 expansion) with higher)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:38
13	90	semiconductor & (chip with (GaN near5 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:39
14	81	(LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:39
15	28	((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))) & (thermal near3 expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:40
16	28	((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))) & (thermal near3 expansion)) & substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:40

17	11	((((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))) & (thermal near3 expansion)) & substrate) & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:49
18	6	((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))) & ((mount\$3 submount\$3) with (thermal near3 expansion) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:52
19	8	((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5 substrate)))) & ((mount\$3 submount\$3) same (thermal near3 expansion) same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:56
20	9	(semiconductor & (chip with (GaN near5 substrate))) & ((mount\$3 submount\$3) same (thermal near3 expansion) same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:58
21	22	(semiconductor & (chip with (GaN near5 substrate))) & ((mount\$3 submount\$3) & (thermal near3 expansion) & substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:17
22	127803	semiconductor with laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:17
23	5486	((GaN nitride) with substrate) & (semiconductor with laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:36
24	4157	((GaN nitride) near7 substrate) & (semiconductor with laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:41
25	658	((GaN nitride) near7 substrate) & (semiconductor with laser)) & (thermal near3 expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:19
26	15	((GaN nitride) near7 substrate) & (semiconductor with laser)) & ((thermal near3 expansion) with higher with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:37
27	10242	((GaN nitride) & substrate) & (semiconductor with laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:37
28	0	((GaN nitride) & substrate) & (semiconductor with laser)) & ((thermal near3 expansion) with (higher near7 than) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:38
29	0	(semiconductor with laser) & ((thermal near3 expansion) with (higher near7 than) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:39
30	0	semiconductor & ((thermal near3 expansion) with (higher near7 than) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:39

31	0	((thermal near3 expansion) with (higher near7 than) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:40
32	0	((thermal near3 expansion) with (higher adj than) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:40
33	824	((thermal near3 expansion) with (higher) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:40
34	49	(semiconductor with laser) & (((thermal near3 expansion) with (higher) with substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:40
35	15	((GaN nitride) near7 substrate) & ((semiconductor with laser) & (((thermal near3 expansion) with (higher) with substrate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 14:41
-	1422619	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:14
-	500623	LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:16
-	79815	semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:16
-	33299	(semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:17
-	3281	semiconductor near3 laser near3 chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:17
-	708	((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & laser) & (semiconductor near3 laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:18
-	41968	(semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:19
-	11793	((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:45
-	157	((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:20

-	156	(((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)) & (layer\$1 stack\$3 chip\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:23
-	41	(((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)) & (layer\$1 stack\$3 chip\$3)) & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:45
-	7	(((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)) & solder\$3) & ((nitri\$3 near3 bas\$3) nitridebased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:47
-	7	(((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)) & solder\$3) & ((nitri\$3 near3 bas\$3) (nitride-based))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:47
-	41	(((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)) & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:46
-	1441160	semiconductor\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:47
-	422761	light\$3 near3 emitt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:48
-	95809	semiconductor\$3 & (light\$3 near3 emitt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:48
-	493	(semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:49
-	140	((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))) & (GaN (nitride adj bas\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:52
-	136	((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))) & (GaN (nitride adj bas\$3)) & substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:52
-	94	((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))) & ((GaN (nitride adj bas\$3)) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:53
-	94	((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))) & ((GaN (nitride adj bas\$3)) with substrate)) & (layer\$1 chip\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 10:54

-	17	(((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3 expansion))) & ((GaN (nitride adj bas\$3). with substrate)) & (layer\$1 chip\$3)) & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 11:25
-	7	"6326638"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 11:26
-	0	"6326638" & (thermal near3 expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 11:26
-	2	"6326638" & solder\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 11:27
-	2	("6326638" & solder\$3) & substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 13:25